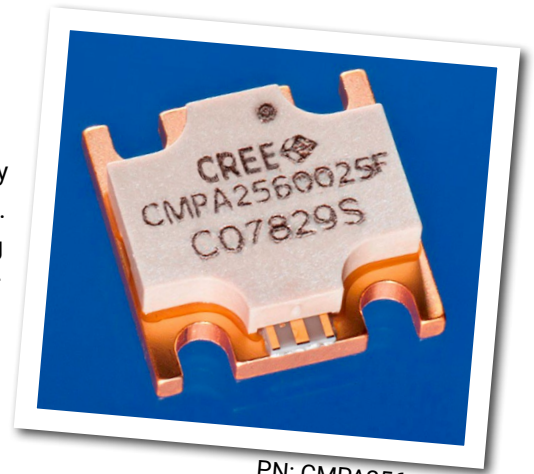


# CMPA2560025F

## 25 W, 2500 - 6000 MHz, GaN MMIC Power Amplifier

Cree's CMPA2560025F is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT) based monolithic microwave integrated circuit (MMIC). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity and higher thermal conductivity. GaN HEMTs also offer greater power density and wider bandwidths compared to Si and GaAs transistors. This MMIC contains a two-stage reactively matched amplifier enabling very wide bandwidths to be achieved in a small footprint screw-down package featuring a Copper-Tungsten heat-sink.



PN: CMPA2560025F  
Package Type: 780019

### Typical Performance Over 2.5-6.0 GHz ( $T_c = 25^\circ\text{C}$ )

Parameter	2.5 GHz	4.0 GHz	6.0 GHz	Units
Gain	27.5	24.3	23.1	dB
Saturated Output Power, $P_{SAT}^1$	35.8	37.5	25.6	W
Power Gain @ $P_{OUT} 43 \text{ dBm}$	23.1	20.9	16.3	dB
PAE @ $P_{OUT} 43 \text{ dBm}$	31.5	32.8	30.7	%

Note1:  $P_{SAT}$  is defined as the RF output power where the device starts to draw positive gate current in the range of 7-13 mA.

### Features

- 24 dB Small Signal Gain
- 25 W Typical  $P_{SAT}$
- Operation up to 28 V
- High Breakdown Voltage
- High Temperature Operation

### Applications

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers

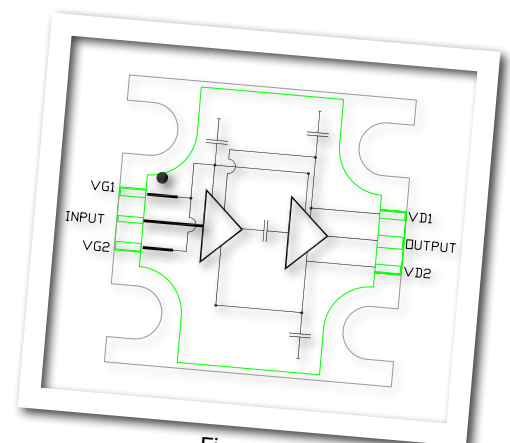


Figure 1.

## Absolute Maximum Ratings (not simultaneous) at 25°C

Parameter	Symbol	Rating	Units
Drain-source Voltage	$V_{DS}$	84	VDC
Gate-source Voltage	$V_{GS}$	-10, +2	VDC
Storage Temperature	$T_{STG}$	-65, +150	°C
Operating Junction Temperature	$T_J$	225	°C
Forward Gate Current	$I_G$	13	mA
Screw Torque	T	40	in-oz
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	°C/W

## Electrical Characteristics (Frequency = 2.5 GHz to 6.0 GHz unless otherwise stated; $T_c = 25^\circ\text{C}$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics</b>						
Gate Threshold Voltage	$V_{(GS)TH}$	-3.8	-3.0	-2.3	V	$V_{DS} = 10\text{ V}, I_D = 20\text{ mA}$
Gate Quiescent Voltage	$V_{(GS)Q}$	-	-2.7	-	VDC	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}$
Drain-Source Breakdown Voltage	$V_{BD}$	84	100	-	V	$V_{GS} = -8\text{ V}, I_D = 20\text{ mA}$
Saturated Drain Current <sup>1</sup>	$I_{DC}$	8.0	9.7	-	A	$V_{DS} = 6.0\text{ V}, V_{GS} = 2.0\text{ V}$
<b>RF Characteristics<sup>2</sup></b>						
Small Signal Gain	S21	19.5	24	-	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}$
Input Return Loss	S11	-	-8	-5	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}$
Output Return Loss	S22	-	-8	-3	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}$
Power Output <sub>1</sub>	$P_{OUT}$	22.0	30	-	W	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 4.0\text{ GHz}$
Power Output <sub>2</sub>	$P_{OUT}$	12.5	17	-	W	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 5.0\text{ GHz}$
Power Output <sub>3</sub>	$P_{OUT}$	15.5	20	-	W	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 6.0\text{ GHz}$
Power Added Efficiency <sub>1</sub>	PAE	34	40	-	%	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 4.0\text{ GHz}$
Power Added Efficiency <sub>2</sub>	PAE	20	26	-	%	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 5.0\text{ GHz}$
Power Added Efficiency <sub>3</sub>	PAE	24	30	-	%	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 6.0\text{ GHz}$
Power Gain <sub>1</sub>	$G_p$	17.5	18.8	-	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 4.0\text{ GHz}$
Power Gain <sub>2</sub>	$G_p$	15.0	16.3	-	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 5.0\text{ GHz}$
Power Gain <sub>3</sub>	$G_p$	16.0	17.0	-	dB	$V_{DD} = 28\text{ V}, I_D = 1200\text{ mA}, P_{IN} = 26\text{ dBm}, \text{Freq} = 6.0\text{ GHz}$
Output Mismatch Stress	VSWR	-	-	5 : 1	$\Psi$	No damage at all phase angles, $V_{DD} = 28\text{ V}, I_{DQ} = 1200\text{ mA}, P_{IN} = 26\text{ dBm}$

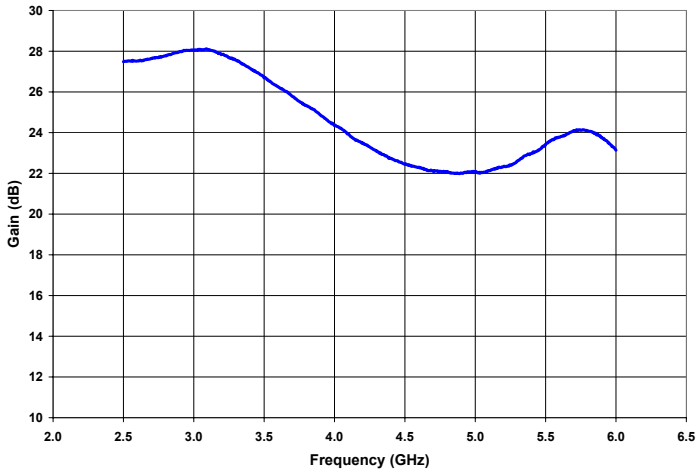
Notes:

<sup>1</sup> Scaled from PCM data.

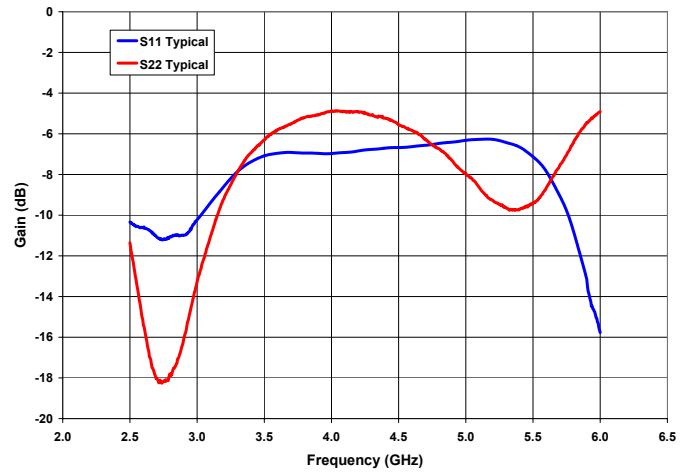
<sup>2</sup> All data CW tested in CMPA2560025F-AMP.

## Typical Performance

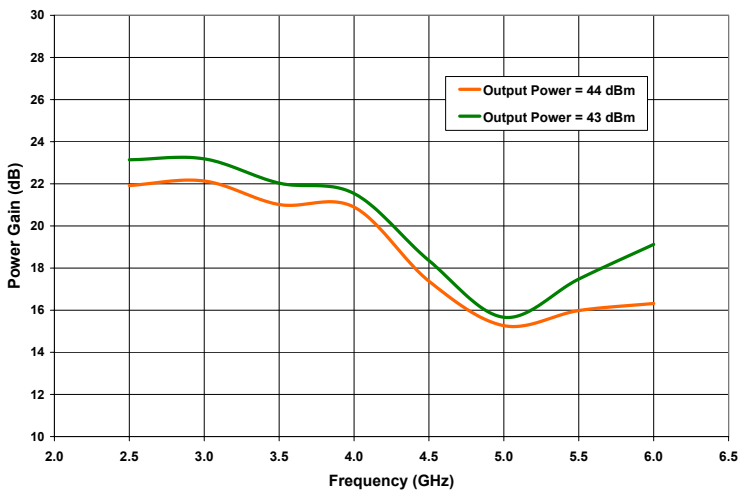
### Small Signal Gain vs Frequency



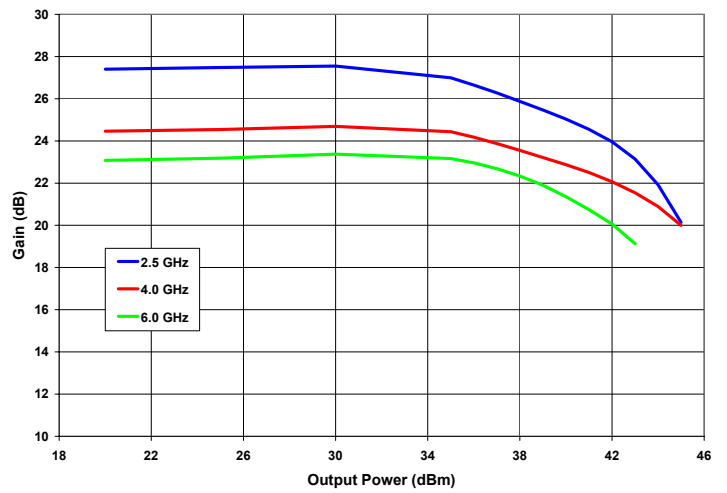
### Input & Output Return Losses vs Frequency



### Power Gain vs Frequency

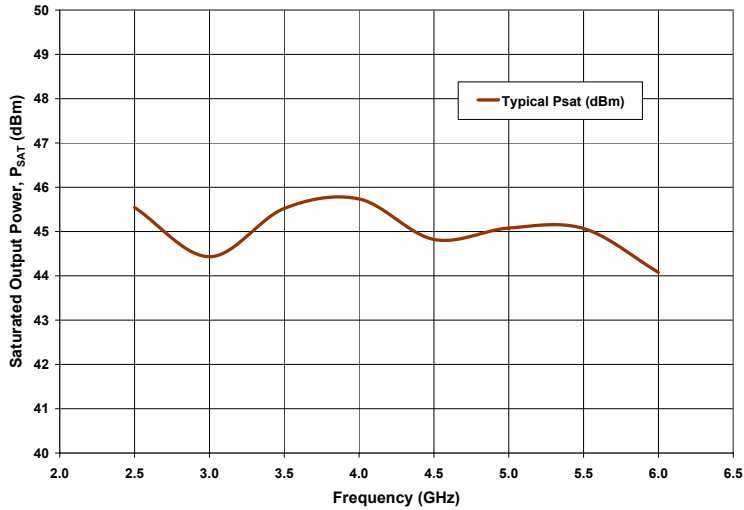


### Gain vs Output Power as a Function of Frequency



## Typical Performance

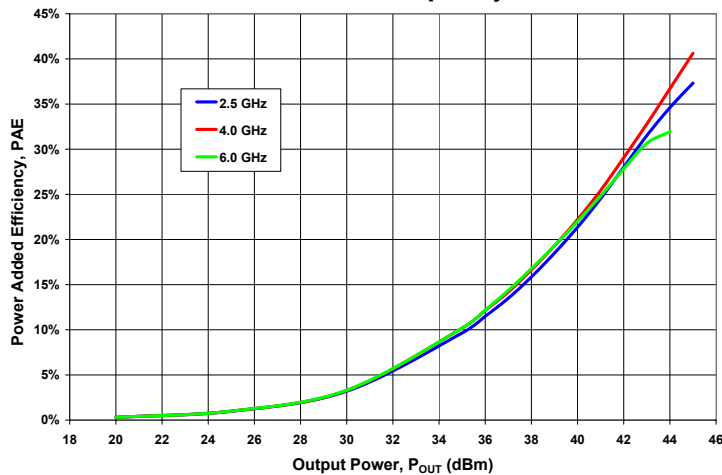
### Saturated Output Power Performance ( $P_{SAT}$ ) vs Frequency



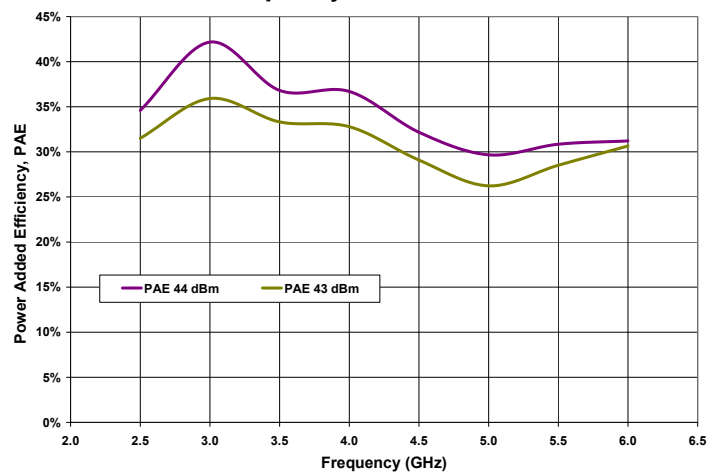
Frequency (GHz)	$P_{SAT}$ (dBm)	$P_{SAT}$ (W)
2.5	45.54	35.8
3.0	44.43	27.7
3.5	45.52	35.7
4.0	45.74	37.5
4.5	44.82	30.4
5.0	45.08	32.2
5.5	45.07	32.1
6.0	44.08	25.6

Note:  $P_{SAT}$  is defined as the RF output power where the device starts to draw positive gate current in the range of 7-13 mA.

### Power Added Efficiency vs Output Power as a Function of Frequency

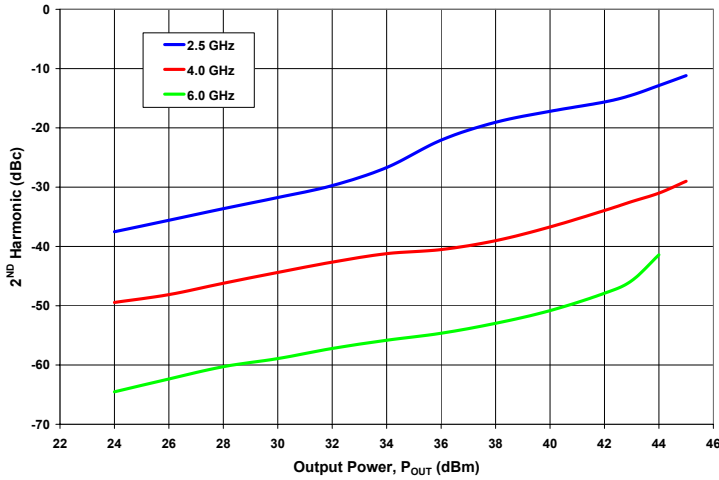


### PAE at 43 dBm and 44 dBm Output Power vs Frequency

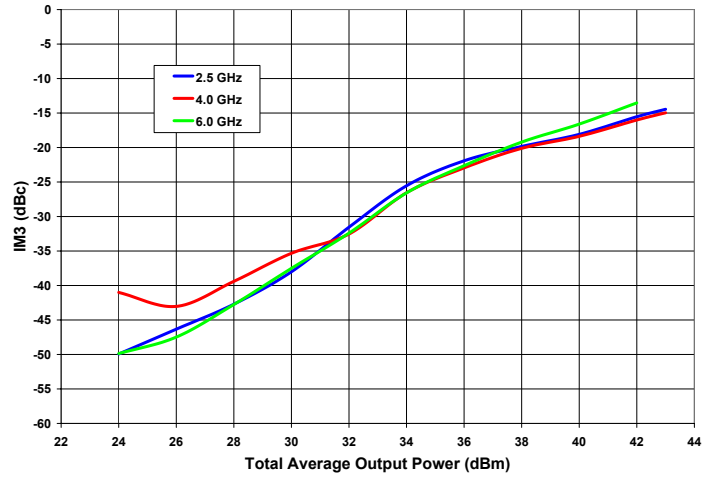


## Typical Performance

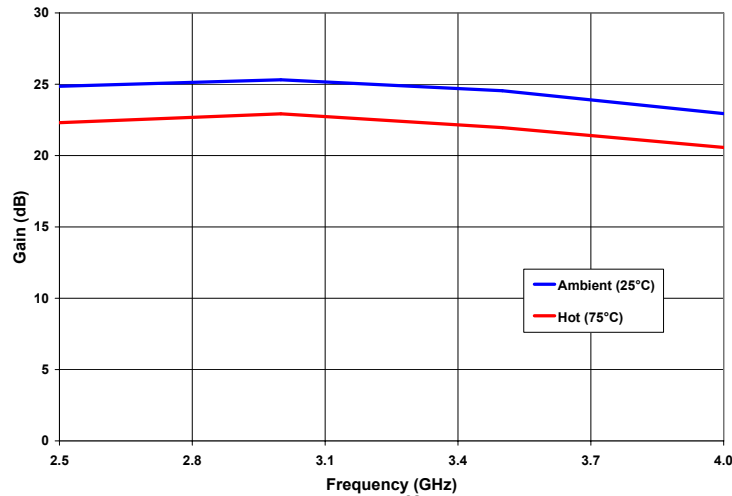
**2<sup>ND</sup> Harmonic vs Output Power as a Function of Frequency**



**IM3 vs Total Average Power as a Function of Frequency**



**Gain at P<sub>OUT</sub> of 40 dBm at 25°C & 75°C vs Frequency**



Note: The temperature coefficient is -0.05 dB/°C

## General Device Information

The CMPA2560025F is a two stage GaN HEMT MMIC Power Amplifier, which operates between 2.5- 6.0 GHz. The amplifier typically provides 25 dB of small signal gain and 25 W saturated output power with an associated power added efficiency of better than 30 %. The wideband amplifier's input and output are internally matched to 50 Ohm. The amplifier requires bias from dedicated ports. The RF-input and output both require an external DC-block. DC voltage should not be applied to the RF output pin due to the internal matching elements. The two gate pins, G1 and G2, are internally connected so it is sufficient to apply bias to only one of them. The drain pins, D1 and D2, should both be connected to the drain supply. The component has internal DC-decoupling on the gate and drain pins, 1840pF and 920pF respectively. The test fixture also provides extra decoupling capacitors on all supply lines. Details of these components can be found on the bill of materials.

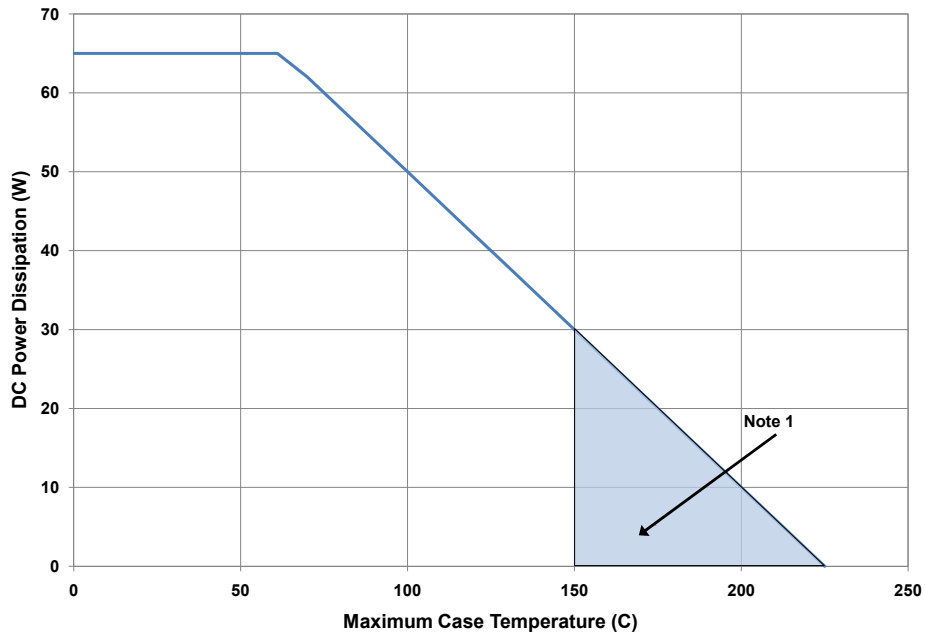
The CMPA2560025F is provided in a lead-less package format. The input and output connections are gold plated to enable gold bond wire attach at the next level assembly.

The measurements in this data sheet were taken on devices wire-bonded to the test fixture with 2 mil gold bond wires. All losses associated with the test fixture are included in the measurements.

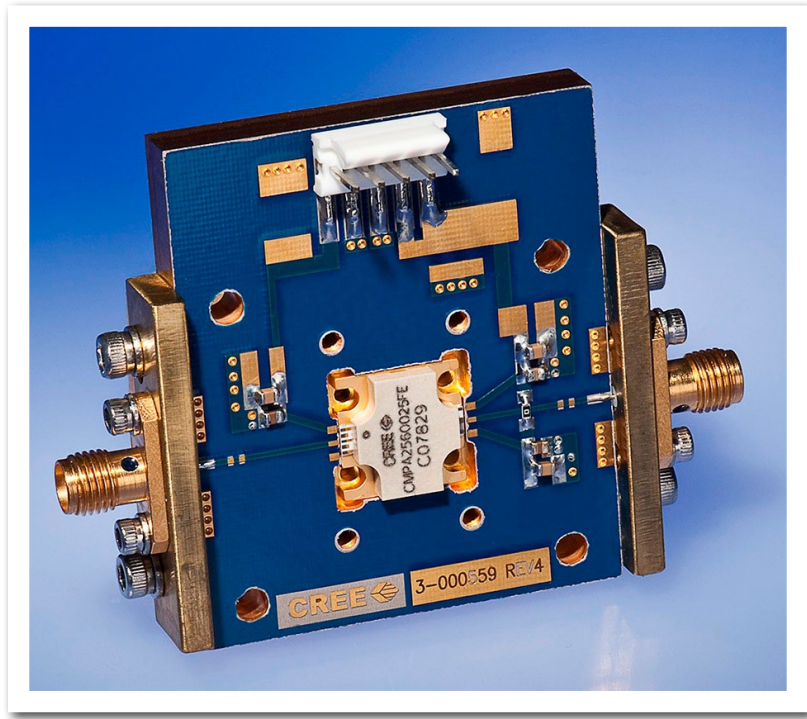
## Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A (> 250 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (200 < 500 V)	JEDEC JESD22 C101-C

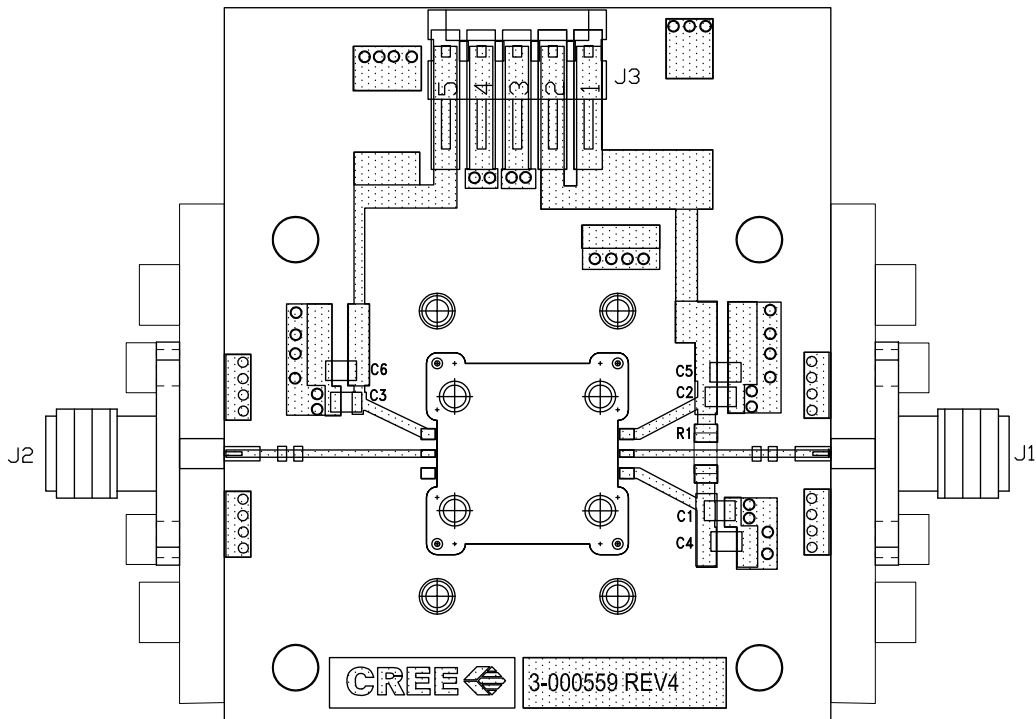
## CMPA2560025F CW Power Dissipation De-rating Curve



## CMPA2560025F-AMP Demonstration Amplifier Circuit



## CMPA2560025F-AMP Demonstration Amplifier Circuit Outline





## CMPA2560025F-AMP Demonstration Amplifier Circuit Bill of Materials

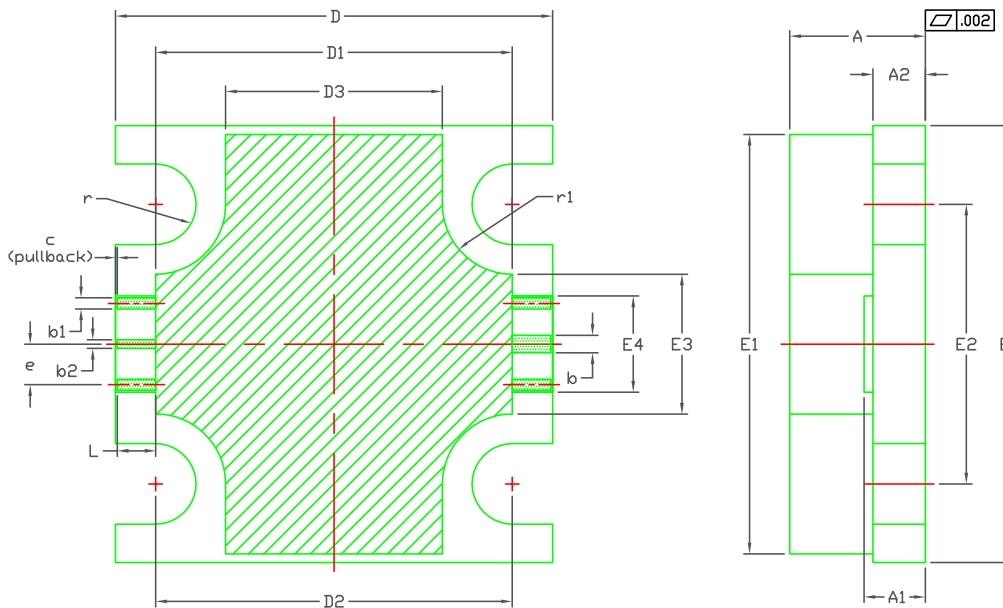
Designator	Description	Qty
J1,J2	CONNECTOR, SMA, AMP1052901-1	2
J3	HEADER, RT. PLZ. 1, CEN LK, 5 POS	1
C1,C2,C3	CAP, 2400 pF, BROADBAND BLOCK, C08BL242X-5UN-X0T 2	3
C4,C5,C6	CAP, 0.1 UF, +/- 10 % , 0805	3
R1	RES, 0 OHM, 1206	1
-	PCB, TACONIC, RF-35-0100-CH/CH	1
Q1	CMPA2560025F	1

### Notes

<sup>1</sup>The CMPA2560025F is connected to the PCB with 2.0 mil Au bond wires.

<sup>2</sup>An external DC Block is required on the input and output.

## Product Dimensions CMPA2560025F (Package Type – 780019)

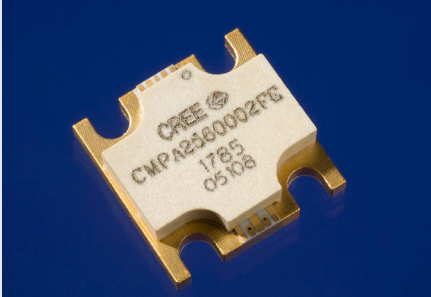
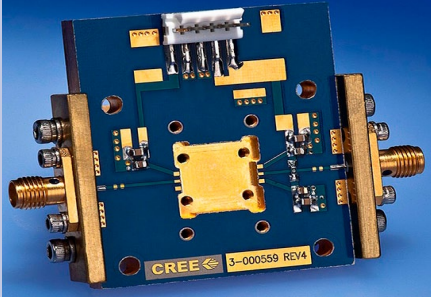
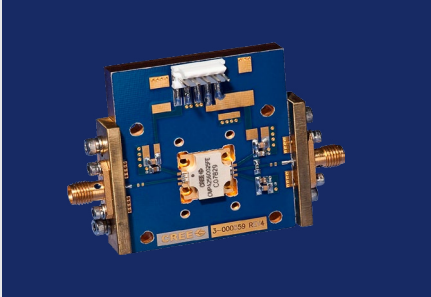


### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
- LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
- ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS		NOTE
	MIN	MAX	MIN	MAX	
A	0.148	0.162	3.76	4.12	—
A1	0.066	0.076	1.67	1.93	—
A2	0.056	0.064	1.42	1.63	—
b	0.022	0.022	0.56	0.56	—
b1	0.013	0.013	0.33	0.33	x4
b2	0.010	0.010	0.25	0.25	—
c	0.002	0.002	0.05	0.05	x2
D	0.495	0.505	12.57	12.83	—
D1	0.403	0.413	10.23	10.49	—
D2	0.408	0.408	10.36	10.36	—
D3	0.243	0.253	6.17	6.43	—
E	0.495	0.505	12.57	12.83	—
E1	0.475	0.485	12.06	12.32	—
E2	0.320	0.320	8.13	8.13	—
E3	0.155	0.165	3.93	4.19	—
E4	0.105	0.115	2.66	2.92	—
e	0.046	0.046	1.17	1.17	x4
L	0.044	0.044	1.12	1.12	x6
r	R0.046	R0.046	R1.17	R1.17	x4
r1	R0.080	R0.080	R2.03	R2.03	x4

## Product Ordering Information

Order Number	Description	Unit of Measure	Image
CMPA25650025F	GaN HEMT	Each	
CMPA2560025F-TB	Test board without GaN HEMT	Each	
CMPA2560025F-AMP	Test board with GaN HEMT installed	Each	



## Disclaimer

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